

IN THE CLAIMS:

1. (Currently Amended) A vacuum processing apparatus for applying a predetermined process to an object (W) to be processed which is placed on a substantially circular placement stage (3) provided in a vacuum chamber (2) by supplying a process gas to the vacuum chamber (2),

characterized in that wherein:

 said vacuum chamber (2) has a substantially circular exhaust port (9) under said placement stage (3), the exhaust port having a diameter equal to or smaller than a diameter of said placement stage (3); and

 a center axis (C1) of said exhaust port (9) is displaced from a center axis (C2) of said placement stage (3); and

a foot-print of said placement stage covers a portion of said exhaust port.

2. (Currently Amended) The vacuum processing apparatus as claimed in claim 1,

characterized in that wherein: [[;]]

 a support part (6) is provided ~~so as~~ to support said placement stage (3) by extending from a side wall (63) of said vacuum chamber (2) toward ~~the~~ a center of said vacuum chamber (2); and

 a direction of displacement of the center axis (C1) of said exhaust port (9) with respect to the center axis (C2) of said placement stage (3) is a direction opposite to an extending direction of said support part (6).

3. (Currently Amended) The vacuum processing apparatus as claimed in claim 2,

characterized in that wherein said support part (6) has a hollow structure, and a utility supply line is provided therein.

4. (Currently Amended) The vacuum processing apparatus as claimed in claim 3,

characterized in that wherein said utility supply line includes at least one of a gas supply line (52), a cooling medium supply line (65) and a power supply line (43, 44).

5. (Currently Amended) The vacuum processing apparatus as claimed in claim 3, ~~characterized in that wherein~~ said support part (6) is detachably attached to said vacuum chamber (2).
6. (Currently Amended) The vacuum processing apparatus as claimed in one of claims 1 to 5, ~~characterized in that wherein~~ a baffle plate (20) is provided ~~so as to surround~~ said placement stage (3).
7. (Currently Amended) The vacuum processing apparatus as claimed in claim 6, ~~characterized in that wherein~~ said baffle plate (20) has ~~many~~ a plurality of apertures (20a), and an open area ratio on a side to which said exhaust port (9) is displaced is smaller than an open area ratio on ~~the~~ an opposite side to which said exhaust port is displaced.
8. (Currently Amended) The vacuum processing apparatus as claimed in one of claims 1 to 5, ~~characterized in that wherein~~ a displacement (D) of the center axis ($C1$) of said exhaust port (9) with respect to the center axis ($C2$) of said placement stage (3) is equal to or smaller than one eleventh of a diameter of said exhaust port (9).
9. (Currently Amended) The vacuum processing apparatus as claimed in one of claims 1 to 5, ~~characterized in that wherein~~ said exhaust port (9) is connected to a vacuum pump (91) having a capacity to maintain said vacuum chamber (2) at a pressure less than 10 Pa.
10. (Currently Amended) The vacuum processing apparatus as claimed in claim 9, ~~characterized in that wherein~~ said vacuum pump is a turbo-molecular pump (91).
11. (Currently Amended) The vacuum processing apparatus as claimed in one of claims 1 to 5, ~~characterized in that wherein~~ a gas supply part (8) constituting a substantially circular showerhead is provided in said vacuum chamber (2), and a center axis of said showerhead is coincident with the center axis ($C2$) of said placement stage (3).

12. (Currently Amended) The vacuum processing apparatus as claimed in claim 11, ~~characterized in that wherein~~ said placement stage (3) and said gas supply part (8) are configured to supply a film deposition process to said object (W) to be processed.

13. (Currently Amended) The vacuum processing apparatus as claimed in one of claims 1 to 5, ~~characterized in that wherein~~ an upper electrode (8) and a lower electrode (41) are provided ~~so as to face to~~ facing each other, ~~wherein and~~ plasma of a process gas is generated between said upper electrode (8) and said lower electrode (41) ~~so as to apply~~ a film deposition process to said object (W) to be processed by the generated plasma.

14. – 15. (Canceled)